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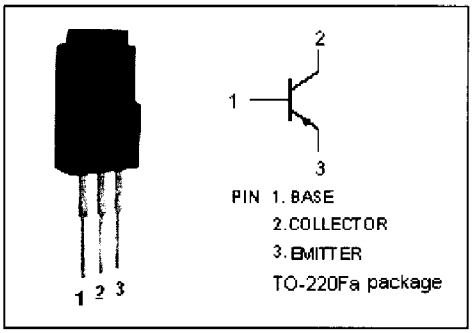
Silicon PNP Power Transistor — 2SA1395



DESCRIPTION

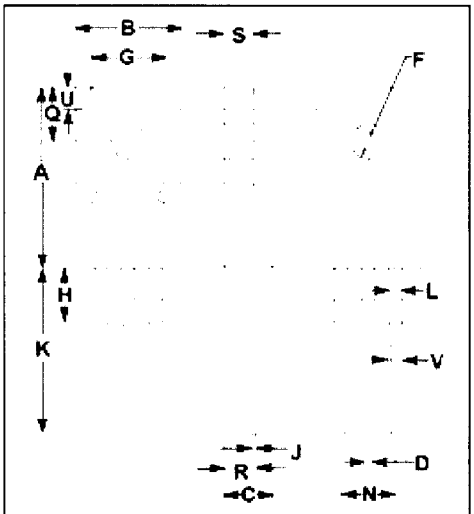
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= −0.6V(Max)@ I_C= -1A
- High Switching Speed
- Complement to Type 2SC3567

APPLICATIONS

- Designed for switching regulator, DC-DC converter and high frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-4	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -1A; I_B= -0.1A, L=1mH	-100		V
$V_{CEX(SUS)-1}$	Collector-Emitter Sustaining Voltage	I_C= -1A; I_{B1}=-I_{B2}= -0.1A, L=180μ H,clamped	-100		V
$V_{CEX(SUS)-2}$	Collector-Emitter Sustaining Voltage	I_C= -2A; I_{B1}= -0.2A; I_{B2}= 0.1A, L=180μ H,clamped	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A		-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1A; I_B= -0.1A		-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V ; I_E=0		-10	μ A
I_{CER}	Collector Cutoff Current	V_{CE}= -100V ; R_{BE}= 51Ω ,T_a=125℃		-1.0	mA
I_{CEX}	Collector Cutoff Current	V_{CE}= -100V; $V_{BE(off)}$= -5V V_{CE}= -100V; $V_{BE(off)}$= -5V,T_a=125℃		-10 -1.0	μ A mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-10	μ A
h_{FE-1}	DC Current Gain	I_C= -0.1A; V_{CE}= -5V	40		
h_{FE-2}	DC Current Gain	I_C= -1A; V_{CE}= -5V	40	200	

Switching times

t_{on}	Turn-on Time	I_C= -1A ,R_L= 50Ω , I_{B1}= -I_{B2}= -0.1A,V_{CC}≈-50V		0.5	μ s
t_{stg}	Storage Time			1.5	μ s
t_f	Fall Time			0.5	μ s

◆ **h_{FE-2} Classifications**

M	L	K
40-80	60-120	100-200